

Abstract of the Disclosure

A magnetic memory device which comprises a magnetic  
5 memory cell that includes a magnetic material switchable  
between two resistive states on the application of a  
magnetic field. The device also comprises a wire that is  
connected to the magnetic memory cell and has a conductive  
connecting link and a conductive word or bit line which  
10 are electrically connected to each other. The connecting  
link is disposed between the word or bit line and the  
magnetic memory cell and has a thermal resistance that is  
larger than that of the word or bit line so as to provide  
a barrier for heat conduction from the magnetic memory  
15 cell to the word or bit line.